

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-17. (Canceled)

18. (Currently Amended) ~~Method~~ A method for recording data by means of an array of micro-tips arranged in a plane facing a memory support, support comprising including a stack of thin layers with at least one deformable memory layer, the method comprising comprising:

data recording by selective actuation of the micro-tips, wherein, the micro-tips being fixed directly onto ~~one and the same~~ one and the same support substrate,substrate; the method comprises

bringing the array of micro-tips and the memory support into contact with a predetermined pressure, which is insufficient to cause a deformation representative of a data to be recorded, before the selective actuation of the micro-tips for data recording, said pressure enabling the dispersion of the dimensions-heights of the micro-tips of the array of micro-tips to be absorbed by the deformable memory layer.

19. (Currently Amended) ~~Method~~ The method according to claim 18, wherein data recording is of electric type.

20. (Currently Amended) ~~Method~~ The method according to claim 18, wherein data recording is of thermal type.

21. (Canceled)

22. (Currently Amended) ~~Recording~~ A recording device for implementation of the method according to claim 18, comprising comprising:

~~an array of micro-tips arranged in a plane facing a memory support, comprising a stack of thin layers with at least one deformable memory layer, means for absorbing the dispersion of the dimensions-heights of the micro-tips of the array array; and~~

~~means for recording by the selective actuation of the micro-tips,~~

~~wherein the deformable memory layer constitutes said means for absorbing when the memory support and the array of micro-tips are brought into contact, at said predetermined pressure, which is insufficient to cause a deformation representative of a data to be recorded,~~

~~the micro-tips, having an apex of nanometric dimension, being fixed directly onto one and the same support substrate.~~

23. (Currently Amended) ~~Device~~ The device according to claim 22, wherein the memory layer is deposited on a flexible layer deposited on the substrate.

24. (Currently Amended) ~~Device~~ The device according to claim 23, wherein the flexible layer is made of polymer.

25. (Currently Amended) ~~Device~~ The device according to claim 24, wherein the flexible layer is made of photoresist.

26. (Currently Amended) ~~Device~~ The device according to claim 23, wherein the flexible layer is a glue of controlled hardness.

27. (Currently Amended) ~~Device~~ The device according to claim 23, wherein the flexible layer is made of elastomer silicone.

28. (Currently Amended) ~~Device~~ The device according to claim 23, wherein the flexible layer has a thickness of about a few micrometers.

29. (Currently Amended) ~~Device~~ The device according to claim 23, wherein the flexible layer is conducting.

30. (Currently Amended) ~~Device~~ The device according to claim 23, further comprising comprising:

_____ an additional conducting layer between the memory layer and the flexible layer.

31. (Currently Amended) ~~Device~~ The device according to claim 22, wherein the memory layer has a thickness of less than one micrometer.

32. (Currently Amended) ~~Device~~ The device according to claim 22, further comprising comprising:

_____ an interface layer with the micro-tips, covering the memory layer.

33. (Currently Amended) ~~Device~~ The device according to claim 22, wherein the substrate is made of silicon.

34. (Currently Amended) ~~Device~~ The device according to claim 22, wherein the substrate is made of plastic material with a thickness of less than one millimeter.